

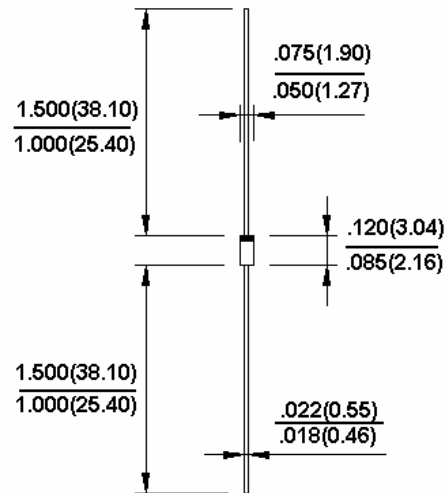
# 1SS133M

## 300mW Hermetically Sealed Glass Switching Diode

### DO-34

### Features

- ◇ Fast switching device( $T_{RR}<4.0nS$ )
- ◇ DO-34 package (JEDEC DO-204)
- ◇ Through-hole device type mounting
- ◇ Hermetically sealed glass
- ◇ Compression bonded construction
- ◇ All external surfaces are corrosion resistant and leads are readily solderable
- ◇ RoHS compliant
- ◇ Solder hot dip Tin (Sn) lead finish
- ◇ Cathode indicated by polarity band



Dimensions in inches and (millimeters)

### Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

#### Maximum Ratings

Type Number	Symbol	Value	Units
Power Dissipation	$P_d$	300	mW
Working Inverse Voltage	$W_{IV}$	90	V
Average Rectified Current	$I_o$	150	mA
Non-Repetitive Peak Forward Current	$I_{FM}$	450	mA
Peak Forward surge Current	$I_{FSURGE}$	2	A
Operating Junction Temperature	$T_J$	+ 175	°C
Storage Temperature Range	$T_{STG}$	-65 to + 200	°C

#### Electrical Characteristics

Type Number	Symbol	Min	Max	Units
Breakdown Voltage $I_R=500nA$	$B_V$	80		V
Forward Voltage $I_F=100mA$	$V_F$		1.2	V
Reverse Leakage Current $V_R=80V$	$I_R$		500	nA
Junction Capacitance $V_R=0, f=1.0MHz$	$C_j$	-	4.0	pF
Reverse Recovery Time (Note 1)	$t_{rr}$	-	4.0	nS

Notes: 1. Reverse Recovery Test Conditions:  $I_F=I_R=10mA$ ,  $R_L=100\Omega$ ,  $I_{RR}=1mA$

## RATINGS AND CHARACTERISTIC CURVES (1SS133M)

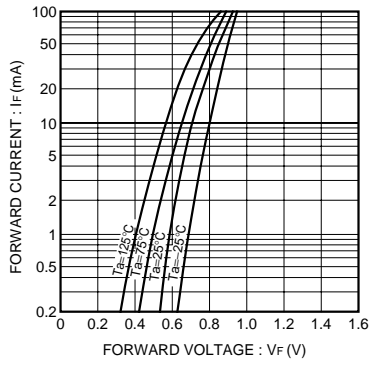


Fig.1 Forward characteristics

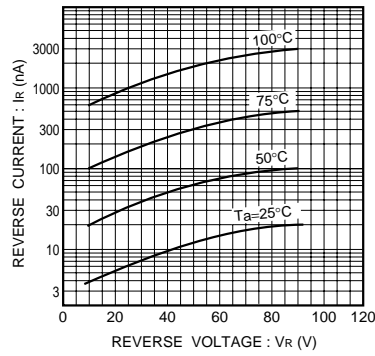


Fig.2 Reverse characteristics

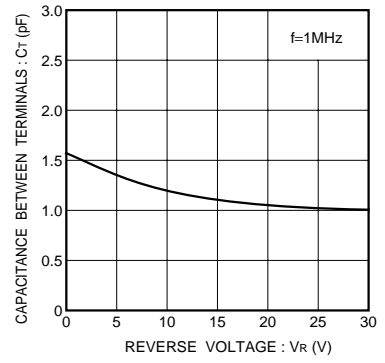


Fig.3 Capacitance between terminals characteristics

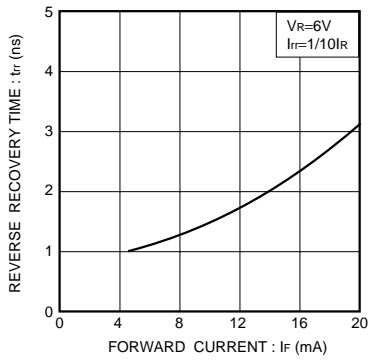


Fig.4 Reverse recovery time characteristics

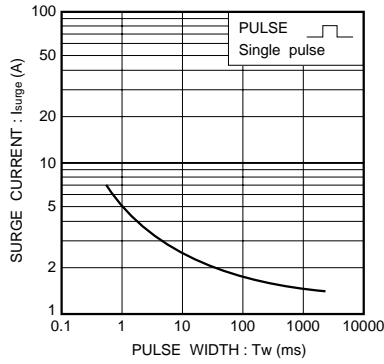


Fig.5 Surge current characteristics

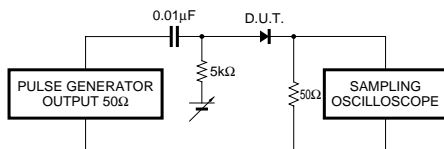


Fig.6 Reverse recovery time ( $t_{rr}$ ) measurement circuit

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